

**SEMICONDUCTOR DEVICES HAVING CAPACITORS OF METAL-
INSULATOR-METAL STRUCTURE WITH COEXTENSIVE OXIDATION
BARRIER PATTERN AND LOWER ELECTRODE BOTTOM AND
METHODS OF FORMING THE SAME**

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Abstract of the Disclosure

A semiconductor device having MIM capacitors is configured so that the bottom surface of the lower electrode and a top surface area of an oxidation barrier pattern are substantially equal. Related methods for forming the device are also

10 described.